

### **Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

### **Listing of Claims:**

1. (Original) A method of growing a gallium nitride single crystal using a flux comprising at least sodium metal; said method comprising the step of:

growing said gallium nitride single crystal in an atmosphere comprising gas mixture comprising nitrogen gas under a total pressure of 300 atms or higher and 2000 atms or lower.

2. (Original) The method of claim 1, wherein said atmosphere has a nitrogen partial pressure of 100 atms or higher and 2000 atms or lower.

3. (Currently Amended) The method of claim 1, wherein said crystal is grown at a temperature of 900 °C or higher and 1500 °C or lower.

4. (Previously Presented) The method of claim 1, wherein said crystal is grown at a temperature of 950 °C or higher and 1200 °C or lower.

5. (Previously Presented) The method of claim 1, further comprising the step of elevating a crucible containing said flux so that a seed crystal contacts said flux.

6. (Previously Presented) The method of claim 1, wherein said gallium nitride single crystal is grown using a system for hot isostatic press.

7. (Canceled)